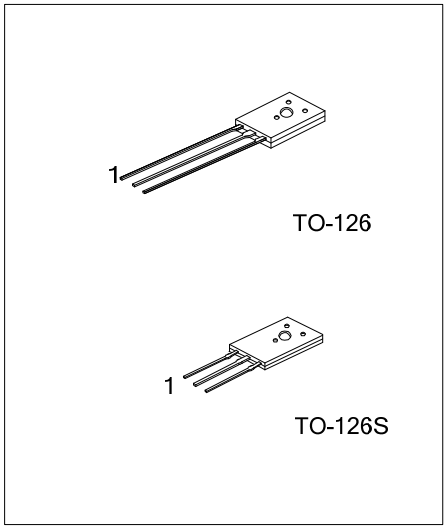
BD237

PNP EPITAXIAL SILICON TRANSISTOR

80V, NPN TRANSISTORS



■ DESCRIPTION

The UTC **BD237** is an NPN transistor. it uses UTC's advanced technology to provide customers with high collector-emitter breakdown voltage, etc.

■ FEATURES

* Complement to UTC **BD238** respectively
* High collector-emitter breakdown voltage

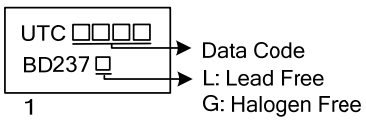
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BD237L-T60-K	BD237G-T60-K	TO-126	E	C	B	Bulk
BD237L-T6S-K	BD237G-T6S-K	TO-126S	E	C	B	Bulk

Note: Pin assignment: E: Emitter B: Base C: Collector

BD237L-T60-K (1) Packing Type (2) Package Type (3) Green Package	(1) K: Bulk (2) T60: TO-126, T6S: TO-126S (3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	2	A
Collector Dissipation	P_C	1.25	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-65~150	°C

Note: Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA, I_E=0	100			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=100mA, I_B=0	80			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA, I_C=0	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=100V, I_E=0			100	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5V, I_C=0			1	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1A, I_B=100mA			0.6	V
DC Current Gain	h_{FE} (1)	I_C=150mA,V_{CE}=2V	40			
	h_{FE} (2)	I_C=1A,V_{CE}=2V	25			
Transition Frequency	f_T	I_C=250mA, V_{CE}=10V, f=10MHz	3			MHz

■ TYPICAL CHARACTERISTICS